

Wide Band Ultra Low Noise Amplifier

4-8GHz



• Gain: 48dB Typ.

• Output P1dB: +15dBm Typ.





RF Parameters				
	Min.	Тур.	Max.	Unit
Frequency Range	4		8	GHz
Gain	45	48		dB
Gain Flatness		±1.5	±3.0	dB
Gain Variation Over Temperature (-45C~+85C)		±1.0		dB
Noise Figure	0.9	1.0	1.1	dB
Input VSWR		1.8	2.5	:1
Output VSWR		1.8	3.0	:1
Output 1 dB Compression Point (P1dB)	13	15		dBm
Saturated Output Power (Psat)		17		dBm
Output Third Order Intercept (IP3)		25		dBm
Supply Current (Vcc=+15V)		165	200	mA
Isolation S12		-55		dB

Physical Specifications				
Weight	1.06 ounces (30g)	Impedance	50 ohms	
Input / Output Connectors	SMA Female	Material	Aluminium	
Finish	Standard: Gold 40 micron; Nickel 220 micron thickness	Package Sealing	Epoxy Sealing	

















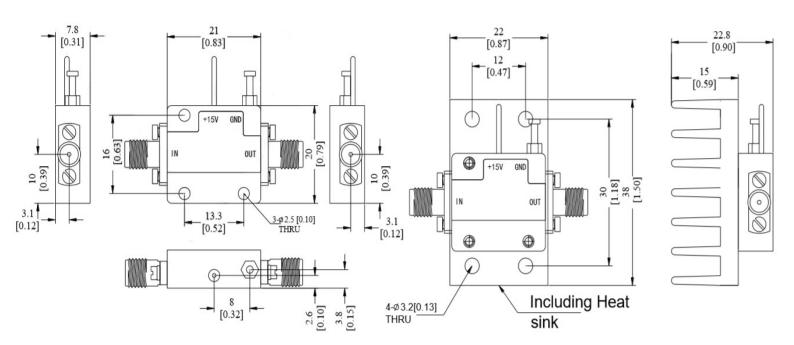
Absolute Maximum Ratings		
Operating Voltage	+15.5V	
RF Input Power (RFIN)	-20dBm	

Biasing Up Procedure		
Step 1	Connect Ground Pin	
Step 2	Connect input and output	
Step 3	Connect +15V biasing	

Power Off Procedure		
Step 1	Turn off +15V biasing	
Step 2	Remove RF connection	
Step 3	Remove Ground	

Environmental		
Operating Temperature	-45°C to +85°C	
Storage Temperature	-55°C to +125°C	
Altitude	30,000 ft. max	
Vibration	25g RMS (15 degree 2KHz) endurance, 1 hour per axis	
Humidity	100% RH at 35°C, 95% RH at 40°C max.	
Shock	20g for 11msec half sine wave, 3 axis both directions	

All Dimensions in mm [inches]
Heat Sink required during operation (Sold separately)



- Note 1: The specification provided is at nominal bias voltage and at 25°C unless otherwise specified
- Note 2: The specification is subject to regular reviews and will be updated from time to time as part of our continuing product development and improved spec accuracy.
- Note 3: Operation beyond the quoted limits stated above may cause instantaneous and permanent damage.











